

Claims:

1. A plasma processing system comprising:
 - a process chamber;
 - an upper electrode assembly;
 - a fluid flow control member; and
 - a chuck assembly including a plurality of lift pin assemblies, for lifting the fluid flow control member at at least one location.
2. The plasma processing system of Claim 1 wherein the chuck assembly comprises at least one of an RF electrode and an electrostatic clamping electrode.
3. The plasma processing system of Claim 1 wherein the fluid flow control member comprises a focus ring.
4. The plasma processing system of Claim 1 wherein the fluid flow control member comprises a pumping baffle.
5. The plasma processing system of Claim 1 wherein the fluid flow control member comprises an auxiliary focus ring.
6. The plasma processing system of Claim 1 wherein lift pins of each of the plurality of lift pin assemblies are lifted simultaneously.
7. The plasma processing system of Claim 1 wherein lift pins of each of the plurality of lift pin assemblies are controllable to be lifted individually.
8. The plasma processing system of Claim 1 wherein the lift pin assemblies comprise motion actuator hardware, bellows and a seal for separating the motion actuator hardware from a plasma in the plasma chamber.
9. The plasma processing system of Claim 1, further comprising a vacuum port located next to at least one of the plurality of lift pin assemblies.

10. In a movable focus ring the improvement comprising:
a hole for facilitating lifting of the focus ring by lift pins.
11. In a movable focus ring the improvement comprising:
a recess for facilitating lifting of the focus ring by lift pins.